

## CAPACITOR

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### BACKGROUND OF THE INVENTION

The present invention relates to a capacitor of an MIM (Metal-Insulator-Metal) structure, more specifically a capacitor which can prevent peeling at the interface between the electrode and the capacitor dielectric film and deterioration of capacitor characteristics due to thermal processing and a method for fabricating the capacitor, and a method for fabricating a semiconductor device including such the capacitor.

DRAM is a semiconductor memory device which can be constituted by one transistor and one capacitor, and have been studied in structures and methods for fabricating semiconductor memory devices of high density and high integration. Especially areas occupied by capacitors much influence integration of devices, so that it is very important how to increase a capacitance per a unit area. To this end, for DRAM of giga-bit storage capacities, which have been recently developed, it has been studied in order to decrease areas occupied by the capacitors that the capacitor dielectric film is formed of metal oxide, whose dielectric constant is higher than those of silicon oxide film and silicon nitride film, which have been conventionally widely used. As such oxide dielectric